

60V N-Channel Enhancement Mode MOSFET

Description

The NP2N7002VR uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications.

General Features

- ◆ $V_{DS} = 60V$, $I_D = 340mA$
 $R_{DS(ON)}(Typ.) = 1.15\Omega @ V_{GS} = 10V$
 $R_{DS(ON)}(Typ.) = 1.25\Omega @ V_{GS} = 4.5V$
- ◆ High power and current handing capability
- ◆ Lead free product is acquired
- ◆ Surface mount package
- ◆ ESD Rating: 2000V HBM

Application

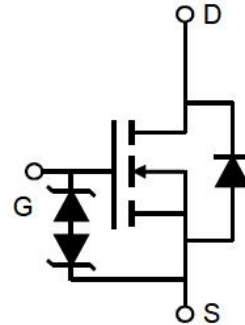
- ◆ PWM applications
- ◆ Load switch

Package

- ◆ SOT-23-3L

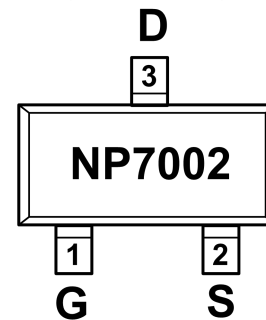


Schematic diagram



Marking and pin assignment

SOT-23-3L
(TOP VIEW)



Ordering Information

| Part Number | Storage Temperature | Package | Devices Per Reel |
|--------------|---------------------|-----------|------------------|
| NP2N7002VR-G | -55°C to +150°C | SOT-23-3L | 3000 |

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

| parameter | symbol | limit | unit |
|--|----------|---------|------|
| Drain-source voltage | V_{DS} | 60 | V |
| Gate-source voltage | V_{GS} | ±20 | V |
| Drain current-continuous ^a @Tj=125°C -pulse ^b | I_D | 0.34 | A |
| | I_{DM} | 0.3 | A |
| Maximum power dissipation | P_D | 0.15 | W |
| Operating junction Temperature range | T_j | -55—150 | °C |

Notes:

- a. surface mounted on FR4 board, $t \leq 10\text{sec}$
- b. pulse test: pulse width $\leq 300\mu\text{s}$, duty $\leq 2\%$

Electrical Characteristics (TA=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|--------------|--|-----|------|----------|----------|
| OFF Characteristics | | | | | | |
| Drain-source breakdown voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 60 | - | - | V |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=48V, V_{GS}=0V$ | - | - | 1 | μA |
| Gate-body leakage | I_{GSS} | $V_{DS}=0V, V_{GS}=\pm 20V$ | - | - | ± 10 | μA |
| ON Characteristics | | | | | | |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 1 | 1.4 | 2.5 | V |
| Drain-source on-state resistance | $R_{DS(ON)}$ | $V_{GS}=10V, I_D=200mA$ | - | 1.15 | 2.5 | Ω |
| | | $V_{GS}=4.5V, I_D=200mA$ | - | 1.25 | 3.5 | |
| Recovered charge | Q_r | $V_{GS}=0V, I_S=300mA$ $V_R=25V$ $dI_S/dt=-100A/\mu S$ | - | 30 | - | nC |
| Dynamic Characteristics | | | | | | |
| Input capacitance | C_{ISS} | $V_{DS}=30V, V_{GS}=0V$ $f=1.0MHz$ | - | 14.8 | - | pF |
| Output capacitance | C_{OSS} | | - | 3.6 | - | |
| Reverse transfer capacitance | C_{RSS} | | - | 2.1 | - | |
| Switching Characteristics | | | | | | |
| Turn-on delay time | $t_{D(ON)}$ | $V_{DD}=5V$ $V_{GS}=10V$ $R_L=250\Omega$ $R_{GEN}=50\Omega$ | - | - | 10 | ns |
| Rise time | t_r | | - | 30 | - | |
| Turn-off delay time | $t_{D(OFF)}$ | | - | - | 15 | |
| Total gate charge | Q_g | $V_{DS}=30V, I_D=200mA$ $V_{GS}=10V$ | - | 1.3 | - | nC |
| Gate-source charge | Q_{gs} | | - | 0.4 | - | |
| Gate-drain charge | Q_{gd} | | - | 0.1 | - | |
| DRAIN-SOURCE DIODE CHARACTERISTICS | | | | | | |
| Diode forward voltage | V_{SD} | $V_{GS}=0V, I_S=300mA$ | - | - | 1.5 | V |

Thermal Characteristics

| Parameter | Symbol | Typ | max | Unit |
|--|-----------------|------|-----|---------------|
| Thermal Resistance-Junction to Case | $R_{\theta jc}$ | 1.7 | - | $^{\circ}C/W$ |
| Thermal Resistance junction-to ambient | $R_{\theta Ja}$ | 62.5 | - | |

Typical Performance Characteristics

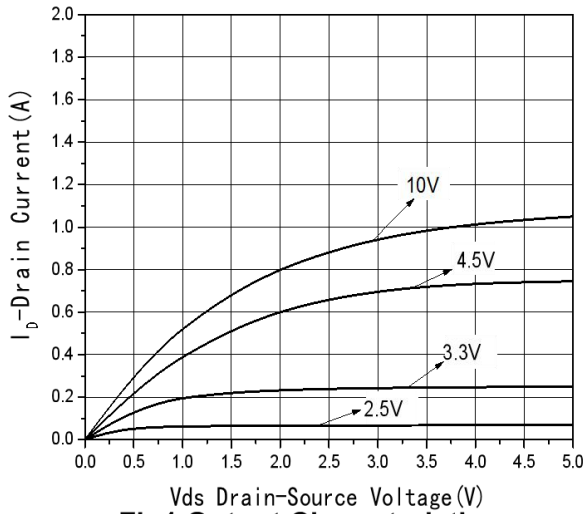


Fig1 Output Characteristics

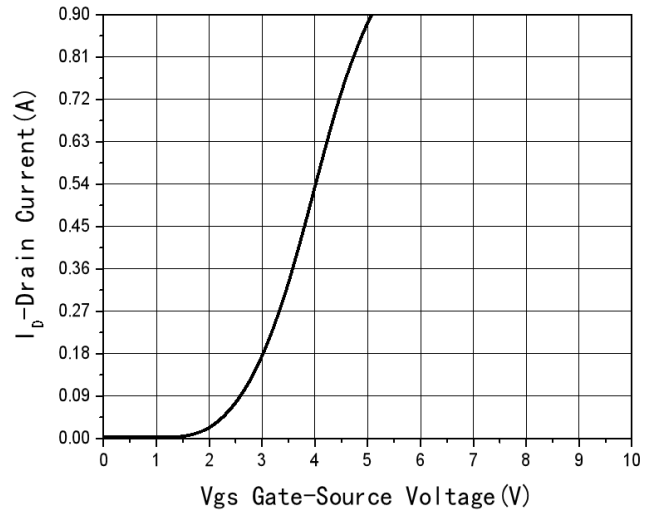


Fig2 Transfer Characteristics

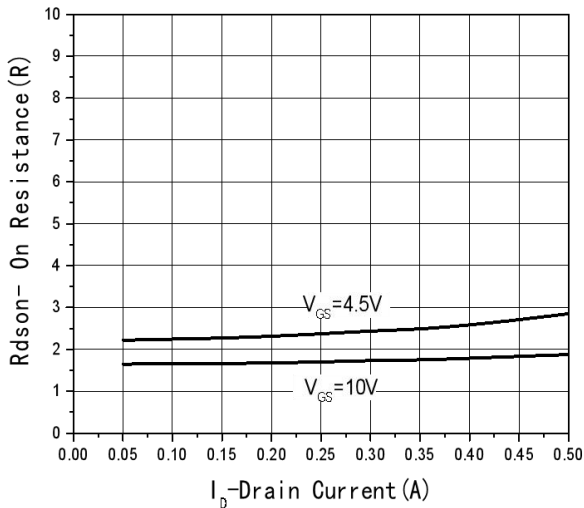


Fig3 $R_{DS(on)}$ -Drain current

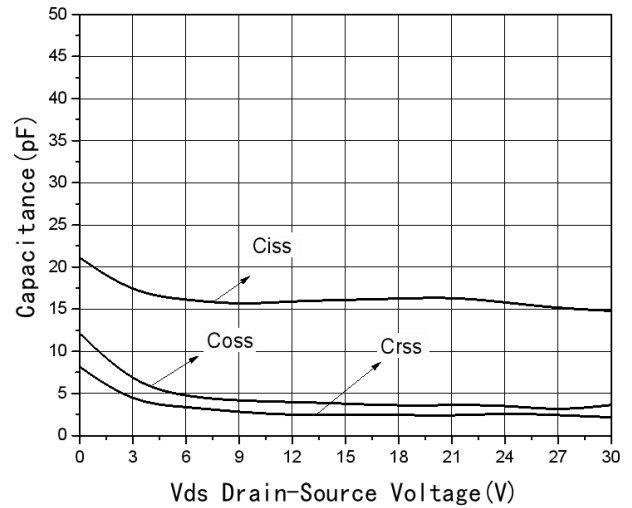


Fig4 Capacitance vs V_{DS}

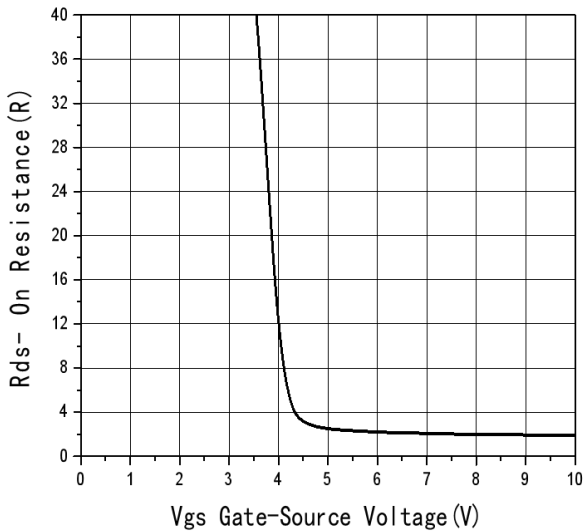


Fig5 $R_{DS(on)}$ -Gate Drain voltage

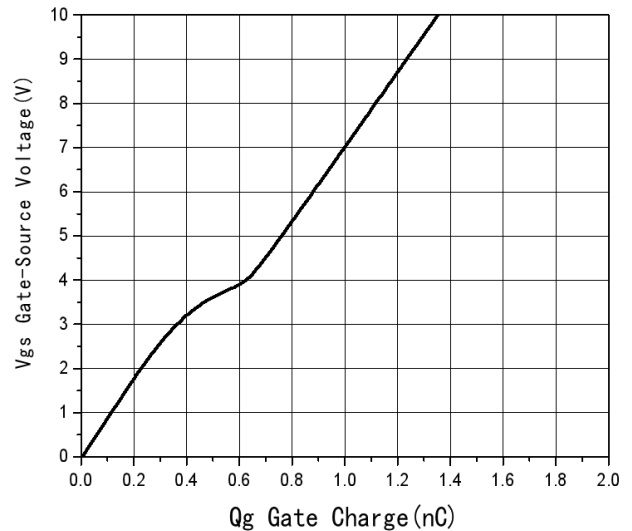


Fig6 Gate Charge

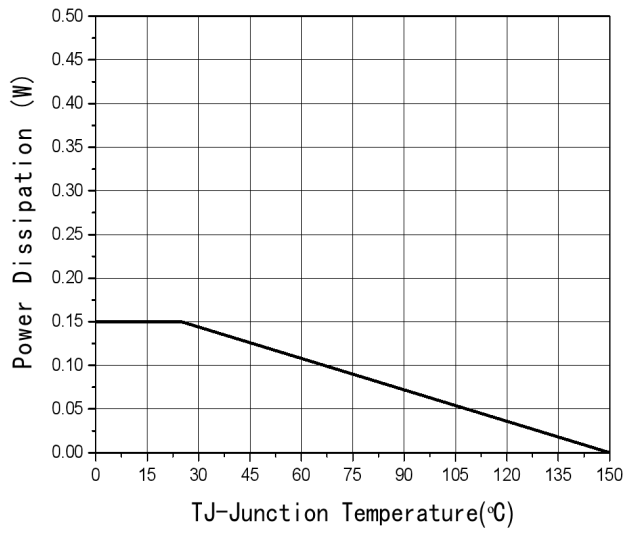


Fig7 Power De-rating

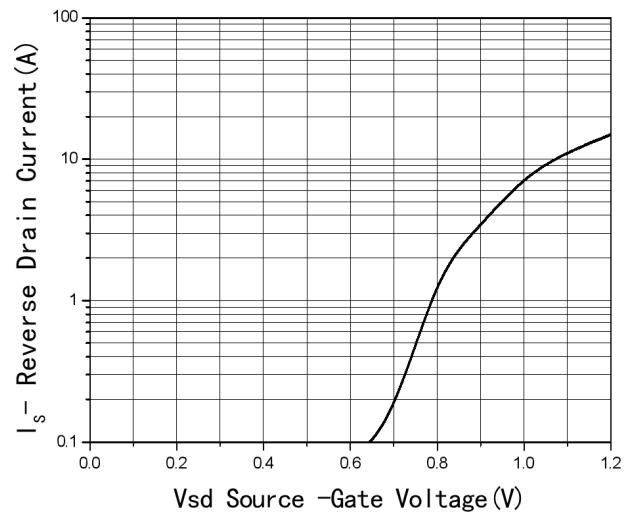
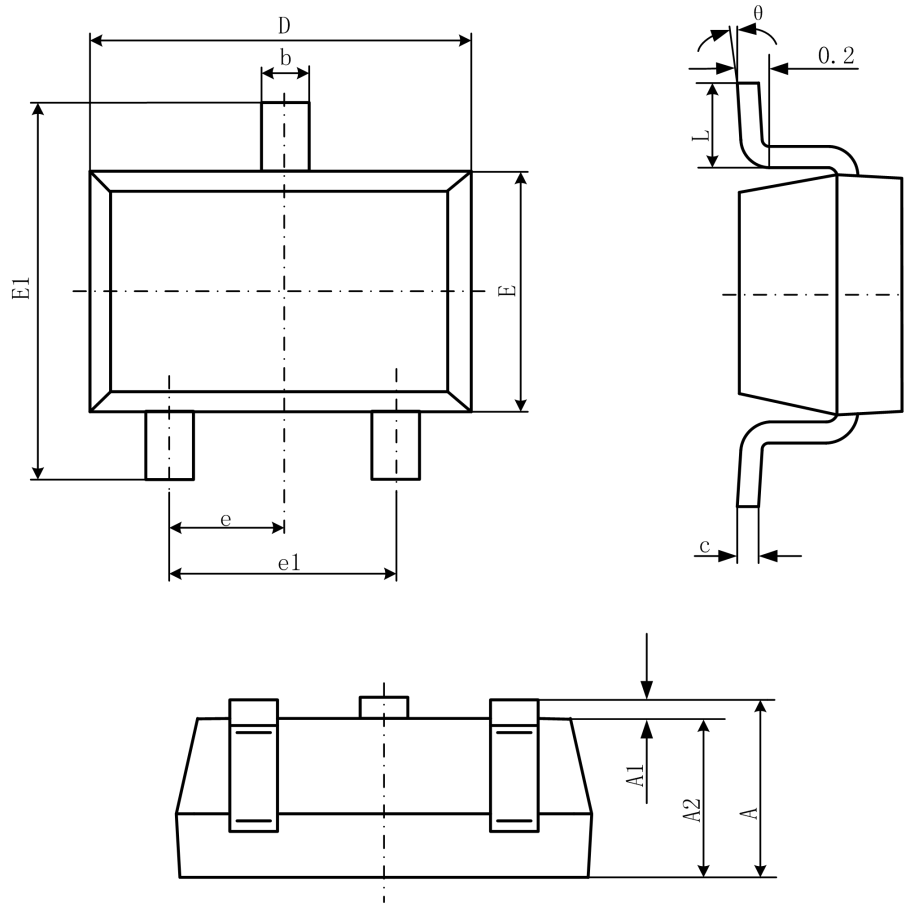


Fig8 Source-Drain Diode Forward

Package Information

- SOT-23-3L



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|----------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.050 | 1.250 | 0.041 | 0.049 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 1.050 | 1.150 | 0.041 | 0.045 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.100 | 0.200 | 0.004 | 0.008 |
| D | 2.820 | 3.020 | 0.111 | 0.119 |
| E | 1.500 | 1.700 | 0.059 | 0.067 |
| E1 | 2.650 | 2.950 | 0.104 | 0.116 |
| e | 0.950(BSC) | | 0.037(BSC) | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.300 | 0.600 | 0.012 | 0.024 |
| θ | 0° | 8° | 0° | 8° |

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